

Thomas Seyller

List of Publications by Year in descending order

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194
papers

21,934
citations

20817

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8630

146
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199
all docs

199
docs citations

199
times ranked

20397
citing authors

#	ARTICLE	IF	CITATIONS
1	Controlling the Electronic Structure of Bilayer Graphene. <i>Science</i> , 2006, 313, 951-954.	12.6	3,003
2	Science and technology roadmap for graphene, related two-dimensional crystals, and hybrid systems. <i>Nanoscale</i> , 2015, 7, 4598-4810.	5.6	2,452
3	Towards wafer-size graphene layers by atmospheric pressure graphitization of silicon carbide. <i>Nature Materials</i> , 2009, 8, 203-207.	27.5	2,396
4	Quasiparticle dynamics in graphene. <i>Nature Physics</i> , 2007, 3, 36-40.	16.7	1,035
5	Interaction, growth, and ordering of epitaxial graphene on SiC{0001} surfaces: A comparative photoelectron spectroscopy study. <i>Physical Review B</i> , 2008, 77, .	3.2	836
6	Interlayer Interaction and Electronic Screening in Multilayer Graphene Investigated with Angle-Resolved Photoemission Spectroscopy. <i>Physical Review Letters</i> , 2007, 98, 206802.	7.8	678
7	Giant Faraday rotation in single- and multilayer graphene. <i>Nature Physics</i> , 2011, 7, 48-51.	16.7	521
8	Friction and Dissipation in Epitaxial Graphene Films. <i>Physical Review Letters</i> , 2009, 102, 086102.	7.8	482
9	Observation of Plasmarons in Quasi-Freestanding Doped Graphene. <i>Science</i> , 2010, 328, 999-1002.	12.6	375
10	Atomic and electronic structure of few-layer graphene on SiC(0001) studied with scanning tunneling microscopy and spectroscopy. <i>Physical Review B</i> , 2008, 77, .	3.2	340
11	Production and processing of graphene and related materials. <i>2D Materials</i> , 2020, 7, 022001.	4.4	333
12	Direct View of Hot Carrier Dynamics in Graphene. <i>Physical Review Letters</i> , 2013, 111, 027403.	7.8	308
13	Raman spectra of epitaxial graphene on SiC(0001). <i>Applied Physics Letters</i> , 2008, 92, .	3.3	305
14	Extended van Hove Singularity and Superconducting Instability in Doped Graphene. <i>Physical Review Letters</i> , 2010, 104, 136803.	7.8	294
15	Reconstruction of Molecular Orbital Densities from Photoemission Data. <i>Science</i> , 2009, 326, 702-706.	12.6	282
16	The quasi-free-standing nature of graphene on H-saturated SiC(0001). <i>Applied Physics Letters</i> , 2011, 99, .	3.3	232
17	Intrinsic Terahertz Plasmons and Magnetoplasmons in Large Scale Monolayer Graphene. <i>Nano Letters</i> , 2012, 12, 2470-2474.	9.1	224
18	Origin of Doping in Quasi-Free-Standing Graphene on Silicon Carbide. <i>Physical Review Letters</i> , 2012, 108, 246104.	7.8	218

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19	Plasmon dispersion and damping in electrically isolated two-dimensional charge sheets. <i>Physical Review B</i> , 2008, 78, .	3.2	211
20	Local work function measurements of epitaxial graphene. <i>Applied Physics Letters</i> , 2008, 93, .	3.3	211
21	Quasiparticle Transformation during a Metal-Insulator Transition in Graphene. <i>Physical Review Letters</i> , 2009, 103, 056404.	7.8	208
22	Doping of single-walled carbon nanotube bundles by Brønsted acids. <i>Physical Chemistry Chemical Physics</i> , 2003, 5, 5472-5476.	2.8	192
23	Epitaxial Graphenes on Silicon Carbide. <i>MRS Bulletin</i> , 2010, 35, 296-305.	3.5	180
24	Structural and electronic properties of graphite layers grown on SiC(0001). <i>Surface Science</i> , 2006, 600, 3906-3911.	1.9	178
25	Symmetry breaking in few layer graphene films. <i>New Journal of Physics</i> , 2007, 9, 385-385.	2.9	174
26	Epitaxial graphene: a new material. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1436-1446.	1.5	173
27	Origin of the energy bandgap in epitaxial graphene. <i>Nature Materials</i> , 2008, 7, 258-259.	27.5	170
28	Quantum oscillations and quantum Hall effect in epitaxial graphene. <i>Physical Review B</i> , 2010, 81, .	3.2	168
29	Coexisting massive and massless Dirac fermions in symmetry-broken bilayer graphene. <i>Nature Materials</i> , 2013, 12, 887-892.	27.5	164
30	Morphology of graphene thin film growth on SiC(0001). <i>New Journal of Physics</i> , 2008, 10, 023034.	2.9	156
31	Raman Topography and Strain Uniformity of Large-Area Epitaxial Graphene. <i>Nano Letters</i> , 2009, 9, 964-968.	9.1	146
32	Highly p-doped epitaxial graphene obtained by fluorine intercalation. <i>Applied Physics Letters</i> , 2011, 98, .	3.3	141
33	Comeback of epitaxial graphene for electronics: large-area growth of bilayer-free graphene on SiC. <i>2D Materials</i> , 2016, 3, 041002.	4.4	135
34	Long Spin Relaxation Times in Wafer Scale Epitaxial Graphene on SiC(0001). <i>Nano Letters</i> , 2012, 12, 1498-1502.	9.1	121
35	Strong Plasmon Reflection at Nanometer-Size Gaps in Monolayer Graphene on SiC. <i>Nano Letters</i> , 2013, 13, 6210-6215.	9.1	121
36	Terahertz Radiation Driven Chiral Edge Currents in Graphene. <i>Physical Review Letters</i> , 2011, 107, 276601.	7.8	118

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37	Growth and electronic structure of boron-doped graphene. <i>Physical Review B</i> , 2013, 87, .	3.2	113
38	On the Way to Grapheneâ€™Pronounced Fluorescence of Polyhydrogenated Graphene. <i>Angewandte Chemie - International Edition</i> , 2013, 52, 754-757.	13.8	108
39	Formation of high-quality quasi-free-standing bilayer graphene on SiC(0 0 1) by oxygen intercalation upon annealing in air. <i>Carbon</i> , 2013, 52, 83-89.	10.3	104
40	Strong phonon-plasmon coupled modes in the graphene/silicon carbide heterosystem. <i>Physical Review B</i> , 2010, 82, .	3.2	103
41	Al ₂ O ₃ prepared by atomic layer deposition as gate dielectric on 6H-SiC(0001). <i>Applied Physics Letters</i> , 2003, 83, 1830-1832.	3.3	98
42	Schottky barrier between 6H-SiC and graphite: Implications for metal/SiC contact formation. <i>Applied Physics Letters</i> , 2006, 88, 242103.	3.3	96
43	Ultrafast Dynamics of Massive Dirac Fermions in Bilayer Graphene. <i>Physical Review Letters</i> , 2014, 112, 257401.	7.8	96
44	Contribution of the buffer layer to the Raman spectrum of epitaxial graphene on SiC(0001). <i>New Journal of Physics</i> , 2013, 15, 043031.	2.9	93
45	Extremely flat band in bilayer graphene. <i>Science Advances</i> , 2018, 4, eaau0059.	10.3	89
46	Electronic and chemical passivation of hexagonal 6H-SiC surfaces by hydrogen termination. <i>Applied Physics Letters</i> , 2001, 78, 1216-1218.	3.3	88
47	Passivation of hexagonal SiC surfaces by hydrogen termination. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S1755-S1782.	1.8	87
48	Effective screening and the plasmaron bands in graphene. <i>Physical Review B</i> , 2011, 84, .	3.2	85
49	Polarization doping of graphene on silicon carbide. <i>2D Materials</i> , 2014, 1, 035003.	4.4	84
50	Epitaxial Growth and Electronic Properties of Large Hexagonal Graphene Domains on Cu(111) Thin Film. <i>Applied Physics Express</i> , 2013, 6, 075101.	2.4	83
51	Tunable Carrier Multiplication and Cooling in Graphene. <i>Nano Letters</i> , 2015, 15, 326-331.	9.1	80
52	High-transconductance graphene solution-gated field effect transistors. <i>Applied Physics Letters</i> , 2011, 99, .	3.3	78
53	Growth and electronic structure of nitrogen-doped graphene on Ni(111). <i>Physical Review B</i> , 2012, 86, .	3.2	77
54	Terahertz ratchet effects in graphene with a lateral superlattice. <i>Physical Review B</i> , 2016, 93, .	3.2	77

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55	Experimental studies of the electronic structure of graphene. <i>Progress in Surface Science</i> , 2009, 84, 380-413.	8.3	75
56	Observation of top-site adsorption for Xe on Cu(111). <i>Chemical Physics Letters</i> , 1998, 291, 567-572.	2.6	74
57	Bottom-gated epitaxial graphene. <i>Nature Materials</i> , 2011, 10, 357-360.	27.5	74
58	The adsorption sites of rare gases on metallic surfaces: a review. <i>Journal of Physics Condensed Matter</i> , 2004, 16, S2839-S2862.	1.8	67
59	Renormalization of graphene bands by many-body interactions. <i>Solid State Communications</i> , 2007, 143, 63-71.	1.9	67
60	Alternative techniques to reduce interface traps in n-type 4H-SiC MOS capacitors. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1378-1389.	1.5	64
61	Automated preparation of high-quality epitaxial graphene on 6H-SiC(0001). <i>Physica Status Solidi (B): Basic Research</i> , 2010, 247, 2924-2926.	1.5	62
62	Localized States Influence Spin Transport in Epitaxial Graphene. <i>Physical Review Letters</i> , 2013, 110, 067209.	7.8	61
63	First results from a second generation toroidal electron spectrometer. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005, 144-147, 1001-1004.	1.7	59
64	A universal transfer route for graphene. <i>Nanoscale</i> , 2014, 6, 889-896.	5.6	58
65	Work function of graphene multilayers on SiC(0001). <i>2D Materials</i> , 2017, 4, 015043.	4.4	58
66	Electronic properties of SiC surfaces and interfaces: some fundamental and technological aspects. <i>Applied Physics A: Materials Science and Processing</i> , 2006, 85, 371-385.	2.3	56
67	Initial Stages of the Graphite-SiC(0001) Interface Formation Studied by Photoelectron Spectroscopy. <i>Materials Science Forum</i> , 2007, 556-557, 525-528.	0.3	55
68	Molecular and electronic structure of PTCDA on bilayer graphene on SiC(0001) studied with scanning tunneling microscopy. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 2064-2067.	1.5	54
69	Mono- and few-layer nanocrystalline graphene grown on Al ₂ O ₃ (0 0 1) by molecular beam epitaxy. <i>Carbon</i> , 2013, 56, 339-350.	10.3	54
70	Dynamical LEED study of Pt(111)-(3 $\sqrt{3}$ \times 3)R30 $^\circ$ -Xe. <i>Physical Review B</i> , 1999, 60, 11084-11088.	3.2	49
71	Synchrotron x-ray photoelectron spectroscopy study of hydrogen-terminated 6H-SiC{0001} surfaces. <i>Physical Review B</i> , 2003, 67, .	3.2	48
72	Observation of 4 nm Pitch Stripe Domains Formed by Exposing Graphene to Ambient Air. <i>ACS Nano</i> , 2013, 7, 10032-10037.	14.6	48

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73	Characteristics of solution gated field effect transistors on the basis of epitaxial graphene on silicon carbide. <i>Journal Physics D: Applied Physics</i> , 2010, 43, 345303.	2.8	47
74	Fabry-Perot enhanced Faraday rotation in graphene. <i>Optics Express</i> , 2013, 21, 24736.	3.4	47
75	Quasi-Freestanding Graphene on SiC(0001). <i>Materials Science Forum</i> , 0, 645-648, 629-632.	0.3	46
76	Quantum size effects in quasi-free-standing Pb layers. <i>Physical Review B</i> , 2007, 75, .	3.2	45
77	Multicomponent magneto-optical conductivity of multilayer graphene on SiC. <i>Physical Review B</i> , 2011, 84, .	3.2	44
78	Direct growth of quasi-free-standing epitaxial graphene on nonpolar SiC surfaces. <i>Physical Review B</i> , 2013, 88, .	3.2	43
79	Friction and atomic-layer-scale wear of graphitic lubricants on SiC(0001) in dry sliding. <i>Wear</i> , 2013, 300, 78-81.	3.1	42
80	Buffer layer free graphene on SiC(0001) via interface oxidation in water vapor. <i>Carbon</i> , 2014, 70, 258-265.	10.3	42
81	Atomic layer deposited aluminum oxide films on graphite and graphene studied by XPS and AFM. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 398-401.	0.8	41
82	Precise control of epitaxy of graphene by microfabricating SiC substrate. <i>Applied Physics Letters</i> , 2012, 101, 041605.	3.3	40
83	Surface-Induced Hybridization between Graphene and Titanium. <i>ACS Nano</i> , 2014, 8, 7704-7713.	14.6	38
84	Ultrafast electron dynamics in epitaxial graphene investigated with time- and angle-resolved photoemission spectroscopy. <i>Journal of Physics Condensed Matter</i> , 2015, 27, 164206.	1.8	37
85	Low-energy electron diffraction study of the multilayer relaxation of Cu(211). <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1999, 17, 1635-1638.	2.1	35
86	Hydrogen terminated $4H\bar{2}SiC(11\bar{1}00)$ and $(112\bar{1}0)$ surfaces studied by synchrotron x-ray photoelectron spectroscopy. <i>Physical Review B</i> , 2005, 71, .	3.2	33
87	Band structure and many body effects in graphene. <i>European Physical Journal: Special Topics</i> , 2007, 148, 5-13.	2.6	32
88	Effect of an intermediate graphite layer on the electronic properties of metal/SiC contacts. <i>Physica Status Solidi (B): Basic Research</i> , 2008, 245, 1369-1377.	1.5	32
89	Dynamical LEED study of $Pd(111)\bar{2}(3\bar{A}-3)R30\hat{A}^{\circ}\bar{2}Xe$. <i>Physical Review B</i> , 2002, 66, .	3.2	30
90	Robust Phonon-Plasmon Coupling in Quasifreestanding Graphene on Silicon Carbide. <i>Physical Review Letters</i> , 2016, 116, 106802.	7.8	30

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91	Interaction of CO ₂ with Cs-promoted Fe(110) as compared to Fe(110)/K+CO ₂ . Surface Science, 1998, 400, 63-79.	1.9	29
92	PES and LEED study of hydrogen- and oxygen-terminated 6H-SiC(0 0 1) and surfaces. Applied Surface Science, 2001, 184, 278-283.	6.1	29
93	Tuning the charge carriers in epitaxial graphene on SiC(0001) from electron to hole via molecular doping with C ₆₀ F ₄₈ . Applied Physics Letters, 2013, 102, .	3.3	29
94	Luminescence, Patterned Metallic Regions, and Photon-Mediated Electronic Changes in Single-Sided Fluorinated Graphene Sheets. ACS Nano, 2014, 8, 7801-7808.	14.6	28
95	Low-temperature ballistic transport in nanoscale epitaxial graphene cross junctions. Applied Physics Letters, 2009, 95, .	3.3	27
96	A momentum space view of the surface chemical bond. Physical Chemistry Chemical Physics, 2011, 13, 3604.	2.8	27
97	Development and character of gap states on alkali doping of molecular films. New Journal of Physics, 2014, 16, 023011.	2.9	27
98	Challenging the Durability of Intermetallic Mo-Ni Compounds in the Hydrogen Evolution Reaction. ACS Applied Materials & Interfaces, 2021, 13, 23616-23626.	8.0	27
99	Ramifications of optical pumping on the interpretation of time-resolved photoemission experiments on graphene. Journal of Electron Spectroscopy and Related Phenomena, 2015, 200, 340-346.	1.7	26
100	Electron-phonon coupling in quasi-free-standing graphene. Journal of Physics Condensed Matter, 2013, 25, 094001.	1.8	25
101	Experimental analysis of the thermal annealing of hard a-C:H films. Diamond and Related Materials, 2014, 45, 43-57.	3.9	25
102	Direct observation of grain boundaries in graphene through vapor hydrofluoric acid (VHF) exposure. Science Advances, 2018, 4, eaar5170.	10.3	25
103	Classical to quantum crossover of the cyclotron resonance in graphene: a study of the strength of intraband absorption. New Journal of Physics, 2012, 14, 095008.	2.9	24
104	Looking behind the scenes: Raman spectroscopy of top-gated epitaxial graphene through the substrate. New Journal of Physics, 2013, 15, 113006.	2.9	24
105	Annealing-induced magnetic moments detected by spin precession measurements in epitaxial graphene on SiC. Physical Review B, 2013, 87, .	3.2	24
106	Rashba splitting of 100-meV in Au-intercalated graphene on SiC. Applied Physics Letters, 2016, 108, .	3.3	24
107	Photoemission Studies of Graphene on SiC: Growth, Interface, and Electronic Structure. , 2008, , 159-170.		24
108	Hydrogenation of 6H-SiC as a surface passivation stable in air. Diamond and Related Materials, 2001, 10, 1291-1294.	3.9	23

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109	Origin of the split Si-H stretch mode on hydrogen terminated 6H-SiC(0001): Titration of crystal truncation. Applied Physics Letters, 2002, 80, 4726-4728.	3.3	23
110	Visualizing Atomic-Scale Negative Differential Resistance in Bilayer Graphene. Physical Review Letters, 2013, 110, 036804.	7.8	23
111	Correlation effects at ideal SiC(0001) (1 $\bar{1}$ -1) surfaces. Physical Review B, 2006, 73, .	3.2	22
112	Porous Ge@C materials via twin polymerization of germanium (<sc>ii</sc>) salicyl alcoholates for Li-ion batteries. Journal of Materials Chemistry A, 2016, 4, 2705-2719.	10.3	21
113	The electronic structure of pentacene revisited. Journal of Electron Spectroscopy and Related Phenomena, 2009, 174, 22-27.	1.7	20
114	Transport properties of high-quality epitaxial graphene on 6H-SiC(0001). Solid State Communications, 2011, 151, 1061-1064.	1.9	20
115	Substrate induced nanoscale resistance variation in epitaxial graphene. Nature Communications, 2020, 11, 555.	12.8	19
116	Adsorption geometry of Cu(111)-(1 $\bar{2}$ -2)-14Xe. Surface Science, 2003, 539, 165-170.	1.9	18
117	Quantitative multichannel NC-AFM data analysis of graphene growth on SiC(0001). Beilstein Journal of Nanotechnology, 2012, 3, 179-185.	2.8	18
118	Low-energy electron diffraction study of krypton on Cu(110). Surface Science, 2000, 454-456, 55-59.	1.9	17
119	Thermal stability of surface and interface structure of atomic layer deposited Al ₂ O ₃ on H-terminated silicon. Journal of Applied Physics, 2007, 102, 094503.	2.5	17
120	Decoupling the Graphene Buffer Layer from SiC(0001) via Interface Oxidation. Materials Science Forum, 0, 717-720, 649-652.	0.3	17
121	Growth and Intercalation of Graphene on Silicon Carbide Studied by Low-Energy Electron Microscopy. Annalen Der Physik, 2017, 529, 1700046.	2.4	17
122	Quasi-Freestanding Graphene on SiC(0001) by Ar-Mediated Intercalation of Antimony: A Route Toward Intercalation of High-Vapor-Pressure Elements. Annalen Der Physik, 2019, 531, 1900199.	2.4	17
123	Silicon Carbide Stacking-Order-Induced Doping Variation in Epitaxial Graphene. Advanced Functional Materials, 2020, 30, 2004695.	14.9	17
124	Interface-induced complex electronic interference structures in Ag films on Ge(111). Physical Review B, 2008, 78, .	3.2	16
125	Structural investigation of nanocrystalline graphene grown on (6 \times 3 $\sqrt{3}$)R30 $^\circ$ -reconstructed SiC surfaces by molecular beam epitaxy. New Journal of Physics, 2013, 15, 123034.	2.9	16
126	Healing of graphene on single crystalline Ni(111) films. Applied Physics Letters, 2014, 105, 191612.	3.3	16

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127	Structural Changes in 2D BiSe Bilayers as n Increases in (BiSe) _{1+δ} (NbSe) ₂ ($n = 1 \times 10^4$) Heterostructures. ACS Nano, 2016, 10, 9489-9499.	14.6	16
128	The adsorption geometry of Ag(111) $\sqrt{7} \times \sqrt{7} R19.1^\circ$ -4Ar studied by LEED. Surface Science, 2001, 475, 891-895.	19.5	15
129	Electronic Structure of Graphite/6H-SiC Interfaces. Materials Science Forum, 2007, 556-557, 701-704.	0.3	15
130	Influence of the growth conditions of epitaxial graphene on the film topography and the electron transport properties. Physica E: Low-Dimensional Systems and Nanostructures, 2010, 42, 687-690.	2.7	15
131	Robust Graphene Membranes in a Silicon Carbide Frame. ACS Nano, 2013, 7, 4441-4448.	14.6	15
132	Manifestation of nonlocal electron-electron interaction in graphene. Physical Review B, 2016, 94, .	3.2	14
133	Synthesis and Properties of (BiSe) _{0.97} MoSe ₂ : A Heterostructure Containing Both 2H-MoSe ₂ and 1T-MoSe ₂ . Chemistry of Materials, 2019, 31, 5824-5831.	6.7	14
134	From a Cerium-Doped Polynuclear Bismuth Oxido Cluster to β -Bi ₂ O ₃ :Ce. Inorganic Chemistry, 2020, 59, 3353-3366.	4.0	14
135	Electronic properties of clean unreconstructed 6H-SiC(0001) surfaces studied by angle resolved photoelectron spectroscopy. Surface Science, 2006, 600, 3845-3850.	1.9	13
136	Ultrafast electronic linewidth broadening in the C π core level of graphene. Physical Review B, 2021, 104, .	4.2	13
137	Wet-Chemical Preparation of Silicate Adlayer Reconstructed SiC(0001) Surfaces as Studied by PES and LEED. Materials Science Forum, 2002, 389-393, 717-720.	0.3	12
138	Interface of atomic layer deposited Al ₂ O ₃ on H-terminated silicon. Physica Status Solidi (A) Applications and Materials Science, 2006, 203, 2194-2199.	1.8	12
139	Preparation and Characterization of Hydrogen Terminated 6H-SiC. Materials Science Forum, 2001, 353-356, 223-226.	0.3	11
140	A High-Resolution Photoemission Study of Hydrogen-Terminated 6H-SiC Surfaces. Materials Science Forum, 2002, 389-393, 713-716.	0.3	11
141	Strain and Charge in Epitaxial Graphene on Silicon Carbide Studied by Raman Spectroscopy. Materials Science Forum, 0, 645-648, 603-606.	0.3	11
142	Spin-resolved photoemission and <i>ab initio</i> theory of graphene/SiC. Physical Review B, 2013, 88, .	3.2	11
143	Surface Transport Properties of Pb-Intercalated Graphene. Materials, 2021, 14, 7706.	2.9	11
144	Morphology and electronic properties of metal organic molecular beam epitaxy grown ZnO on hydrogen passivated 6H-SiC(0001). Journal of Applied Physics, 2008, 103, 103720.	2.5	10

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145	HREELS study of graphene formed on hexagonal silicon carbide. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2010, 7, 394-397.	0.8	10
146	The interaction of quasi-particles in graphene with chemical dopants. <i>New Journal of Physics</i> , 2010, 12, 125014.	2.9	10
147	Detecting the local transport properties and the dimensionality of transport of epitaxial graphene by a multi-point probe approach. <i>Applied Physics Letters</i> , 2013, 102, 033110.	3.3	10
148	CoCrFeNi High-Entropy Alloy Thin Films Synthesised by Magnetron Sputter Deposition from Spark Plasma Sintered Targets. <i>Coatings</i> , 2021, 11, 468.	2.6	10
149	Charge transfer in $(\text{PbSe})_{1+x}\text{I}$ $(\text{NbSe})_2$ and $(\text{SnSe})_{1+x}\text{I}$ $(\text{NbSe})_2$ ferecrystals investigated by photoelectron spectroscopy. <i>Journal of Physics Condensed Matter</i> , 2018, 30, 055001.	1.8	9
150	Small scale rotational disorder observed in epitaxial graphene on SiC(0001). <i>New Journal of Physics</i> , 2013, 15, 023019.	2.9	8
151	Characterization of K and Cs adsorption on Fe(110). <i>Surface Science</i> , 1999, 424, 278-289.	1.9	7
152	Stacking rearrangement at 6H-SiC(0001) surfaces during thermal hydrogenation. <i>Surface Science</i> , 2003, 532-535, 698-704.	1.9	7
153	Initial Stages of Thermal Oxidation of 4H-SiC (11-20) Studied by Photoelectron Spectroscopy. <i>Materials Science Forum</i> , 2004, 457-460, 1317-1320.	0.3	7
154	Photoemission of $\text{Ga}_{1-x}\text{Mn}_x$ As with high Curie temperature and transformation into MnAs of zincblende structure. <i>Physica Status Solidi (B): Basic Research</i> , 2009, 246, 1435-1439.	1.5	7
155	Nickel enhanced graphene growth directly on dielectric substrates by molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016, 120, 045309.	2.5	7
156	Synthesis and Electrical Properties of a New Compound $(\text{BiSe})_{0.97}(\text{Bi}_2\text{Se}_3)_{1.26}(\text{BiSe})_{0.97}(\text{MoSe}_2)_2$ Containing Metallic 1T-MoSe ₂ . <i>Chemistry of Materials</i> , 2021, 33, 6403-6411.		7
157	Implanted bottom gate for epitaxial graphene on silicon carbide. <i>Journal Physics D: Applied Physics</i> , 2012, 45, 154006.	2.8	6
158	The Atomic Structure of the Hydrogen Saturated a-Planes of 4H-SiC. <i>Materials Science Forum</i> , 2004, 457-460, 395-398.	0.3	5
159	Transport Properties of Single-Layer Epitaxial Graphene on 6H-SiC (0001). <i>Materials Science Forum</i> , 2010, 645-648, 637-641.	0.3	5
160	Quasi-freestanding epitaxial graphene transistor with silicon nitride top gate. <i>Journal Physics D: Applied Physics</i> , 2014, 47, 305103.	2.8	5
161	Single Crystalline Metal Films as Substrates for Graphene Growth. <i>Annalen Der Physik</i> , 2017, 529, 1700023.	2.4	5
162	Annealing effects on a-SiC:H and a-SiCN:H films deposited by plasma CVD methods. <i>Vacuum</i> , 2020, 178, 109410.	3.5	5

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163	Surface Band Structure Studies of Si Rich Reconstructions on 4H-SiC(1-100). Materials Science Forum, 2005, 483-485, 547-550.	0.3	4
164	Influence of structural properties on ballistic transport in nanoscale epitaxial graphene cross junctions. Nanotechnology, 2012, 23, 395203.	2.6	4
165	Electronic structure of designed [(SnSe) _{1-x} (TeSe) _x] ₂ heterostructure thin films with tunable layering sequence. Journal of Materials Research, 2019, 34, 1965-1975.	2.6	4
166	Stacking Relations and Substrate Interaction of Graphene on Copper Foil. Advanced Materials Interfaces, 2021, 8, 2002025.	3.7	4
167	Influence of Nanoarchitectures on Interlayer Interactions in Layered Bi ₂ Se ₃ Heterostructures. Journal of Physical Chemistry C, 2021, 125, 9469-9478.	3.1	4
168	Co as Adsorbate and Reaction Product in the Systems Fe(110)/Cs+Co and Fe(110)/Cs+Co ₂ . Surface Review and Letters, 1998, 05, 569-579.	1.1	3
169	Structural and Electronic Properties of the 6H-SiC(0001)/Al ₂ O ₃ Interface Prepared by Atomic Layer Deposition. Materials Science Forum, 2004, 457-460, 1369-1372.	0.3	3
170	How the solid state matrix affects the chemical shift of core-level binding energies: A novel method to take the induction effect into account. Solid State Communications, 2006, 139, 370-375.	1.9	3
171	The interaction of Xe and Xe+K with graphene. Journal of Electron Spectroscopy and Related Phenomena, 2011, 183, 118-124.	1.7	3
172	The Hall coefficient: a tool for characterizing graphene field effect transistors. 2D Materials, 2014, 1, 035004.	4.4	3
173	LEED AND STM STUDY OF Cs ON Cu(211). Surface Review and Letters, 1999, 06, 865-870.	1.1	2
174	Epitaxial growth and the electronic structure of MgSe on ZnSe/GaAs (001). Journal of Electron Spectroscopy and Related Phenomena, 2001, 114-116, 527-532.	1.7	2
175	ALD Deposited Al ₂ O ₃ Films on 6H-SiC(0001) after Annealing in Hydrogen Atmosphere. Materials Science Forum, 2005, 483-485, 559-562.	0.3	2
176	Hydrogen-Saturated SiC-Surfaces: Model Systems for Studies of Passivation, Reconstruction and Interface Formation. Materials Science Forum, 2005, 483-485, 535-540.	0.3	2
177	4H-SiC Metal-Oxide-Semiconductor (MOS) Capacitors Fabricated by Oxidation in a Tungsten Lamp Furnace in Combination with a Microwave Plasma and Subsequent Deposition of Al ₂ O ₃ . Materials Science Forum, 2007, 556-557, 627-630.	0.3	2
178	Graphene Layers on Silicon Carbide Studied by Raman Spectroscopy. Materials Science Forum, 0, 600-603, 567-570.	0.3	2
179	Electronic band structure of Bi-intercalate layers in graphene and SiC(0001). Journal of the Korean Physical Society, 2021, 78, 157-163.	0.7	2
180	Pump-induced terahertz anisotropy in bilayer graphene. Physical Review B, 2022, 105, .	3.2	2

#	ARTICLE	IF	CITATIONS
181	Mapping disorder-induced changes to the Fermi surface of Cu ₃ Au using a new toroidal electron energy analyser. <i>Journal of Electron Spectroscopy and Related Phenomena</i> , 2005, 144-147, 515-518.	1.7	1
182	Publisher's Note: Correlation effects at ideal SiC(0001) (1 $\bar{1}$ -1) surfaces [Phys. Rev. B 73, 075412 (2006)]. <i>Physical Review B</i> , 2006, 73, .	3.2	1
183	Epitaxial Graphene on SiC(0001). <i>Nanoscience and Technology</i> , 2011, , 135-159.	1.5	1
184	Silicon Nitride as Top Gate Dielectric for Epitaxial Graphene. <i>Materials Science Forum</i> , 2013, 740-742, 149-152.	0.3	1
185	Growth of Nanocrystalline MoSe ₂ Monolayers on Epitaxial Graphene from Amorphous Precursors. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1800283.	1.5	1
186	Surface, interface and bulk properties of GaAs(111)B treated by Se layers. <i>Journal Physics D: Applied Physics</i> , 2001, 34, 678-682.	2.8	0
187	Gated Epitaxial Graphene Devices. <i>Materials Science Forum</i> , 2012, 717-720, 675-678.	0.3	0
188	Backside Monitoring of Graphene on Silicon Carbide by Raman Spectroscopy. <i>Materials Science Forum</i> , 2014, 778-780, 1166-1169.	0.3	0
189	Science and Technology of Graphene. <i>Annalen Der Physik</i> , 2017, 529, 1700322.	2.4	0
190	Growth of Nanocrystalline MoSe ₂ Monolayers on Epitaxial Graphene from Amorphous Precursors (Phys. Status Solidi B 2/2019). <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1970015.	1.5	0
191	Surfaces, Interfaces, and Nanostructures: Spectroscopic Characterization and Applications. <i>Physica Status Solidi (B): Basic Research</i> , 2019, 256, 1900027.	1.5	0
192	Anisotropic Terahertz Pump-Probe Response of Bilayer Graphene. , 2021, , .		0
193	Effect of an Intermediate Graphite Layer on the Electronic Properties of Metal/SiC Contacts. , 0, , 35-50.		0
194	Hardness Enhancement in CoCrFeNi _{1-x} (WC) _x High-Entropy Alloy Thin Films Synthesised by Magnetron Co-Sputtering. <i>Coatings</i> , 2022, 12, 269.	2.6	0